

**BC548 BC548A BC548B BC548C** 



# **NPN General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 10. See PN100A for characteristics.

# **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	30	V
V <sub>CES</sub>	Collector-Base Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	500	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- These ratings are based on a maximum junction temperature of 150 degrees C.
  These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		BC548 / A / B / C	
P <sub>D</sub>	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

# NPN General Purpose Amplifier (continued)

$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	ymbol	Parameter	Test Conditions	Min	Max	Units
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	O. I.A	DA OTERIOTION				
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				1	·	1
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	BR)CEO	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	30		V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	BR)CBO	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A},  I_E = 0$	30		V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	BR)CES	Collector-Base Breakdown Voltage	$I_C = 10  \mu A, I_E = 0$	30		V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		Emitter-Base Breakdown Voltage	$I_E = 10  \mu A, I_C = 0$	5.0		V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	0	Collector Cutoff Current	· ·		15	nA
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			$V_{CB} = 30 \text{ V}, I_{E} = 0, T_{A} = +150 ^{\circ}\text{C}$		5.0	μΑ
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	E	Do current dam				
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	E	DC Current Gain				
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$				-	_	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			548C	420	800	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	E(sat)	Collector-Emitter Saturation Voltage	· -			V
$V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA} \qquad 0.77$						V
	BE(on)	Base-Emitter On Voltage		0.58		V
$h_{fe}$ Small-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ 125 900			$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$		0.77	V
$h_{fe}$ Small-Signal Current Gain $I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ 125 900						
	MALL S	IGNAL CHARACTERISTICS				
Ι = Ι.Ο ΚΠΖ			$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$	125	900	
NF Noise Figure $V_{CE} = 5.0 \text{ V}, I_C = 200 \mu\text{A},$ 10		Small-Signal Current Gain	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 1.0 kHz	125	900	
$R_{S} = 2.0 \text{ k}\Omega, \text{ f} = 1.0 \text{ kHz}, \\ B_{W} = 200 \text{ Hz}$	)	Small-Signal Current Gain	f = 1.0  kHz $V_{CE} = 5.0 \text{ V}, I_{C} = 200 \mu\text{A},$	125		dB

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